

#### P-CHANNEL ENHANCEMENT MODE MOSFET

### Product Summary(Typ. @ V<sub>GS</sub> = -4.5V, T<sub>A</sub> = +25°C)

V <sub>DSS</sub>	R <sub>DS(on)</sub>	Qg	$Q_{\mathrm{gd}}$	I <sub>D</sub>
-20V	55mΩ	2.9nC	0.5nC	-3.5A

### **Description and Applications**

This new generation MOSFET is designed to minimize the on-state resistance (R<sub>DS(on)</sub>) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

### **Applications**

- · Battery Management
- · Load Switch
- Battery Protection

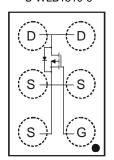
### **Features and Benefits**

- LD-MOS Technology with the Lowest Figure of Merit:  $R_{DS(on)} = 55m\Omega$  to Minimize On-State Losses  $Q_{\alpha} = 2.9nC$  for Ultra-Fast Switching
- V<sub>gs(th)</sub> = -0.6V typ. for a Low Turn-On Potential
- CSP with Footprint 1.5mm x 1.0mm
- Height = 0.62mm for Low Profile
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

#### **Mechanical Data**

- Case: U-WLB1510-6
- Terminal Connections: See Diagram Below
- Weight: 0.0018 grams (Approximate)

#### U-WLB1510-6



Top View

#### Ordering Information (Note 4)

I	Part Number	Case	Packaging		
	DMP2070UCB6-7	U-WLB1510-6	3,000/Tape & Reel		

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

## **Marking Information**

U-WLB1510-6



2W = Product Type Marking Code YM = Date Code Marking Y = Year (ex: Y = 2011) M = Month (ex: 9 = September)

Date Code Key

- 410 0040 . 10,												
Year	201	1	2012		2013	20	14	2015		2016	7	2017
Code	Υ		Z		Α		3	С		D		Е
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

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## Maximum Ratings (@T<sub>A</sub> = +25°C unless otherwise specified.)

Characteristic		Symbol	Value	Units	
Drain-Source Voltage		V <sub>DSS</sub>	-20	V	
Gate-Source Voltage		V <sub>GSS</sub>	±8	V	
Continuous Drain Current (Note 4) V <sub>GS</sub> = -4.5V	Steady State	$T_A = +25$ °C $T_A = +70$ °C	I <sub>D</sub>	-2.5 -2.0	А
Continuous Drain Current (Note 5) $V_{GS} = -4.5V$ Steady $T_A = +25^{\circ}C$ State $T_A = +70^{\circ}C$		I <sub>D</sub>	-3.5 -2.8	А	
Pulsed Drain Current (Note 6)		I <sub>DM</sub>	-12	Α	
Maximum Continuous Body Diode Forward Curren	t (Note 5)	Is	-1.8	А	

### Thermal Characteristics (@TA = +25°C unless otherwise specified.)

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 4)	P <sub>D</sub>	0.92	W
Total Power Dissipation (Note 5)	P <sub>D</sub>	1.47	W
Thermal Resistance, Junction to Ambient (Note 4)	$R_{\theta JA}$	136	°C/W
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	84	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

## **Electrical Characteristics** (@T<sub>A</sub> = +25°C unless otherwise specified.)

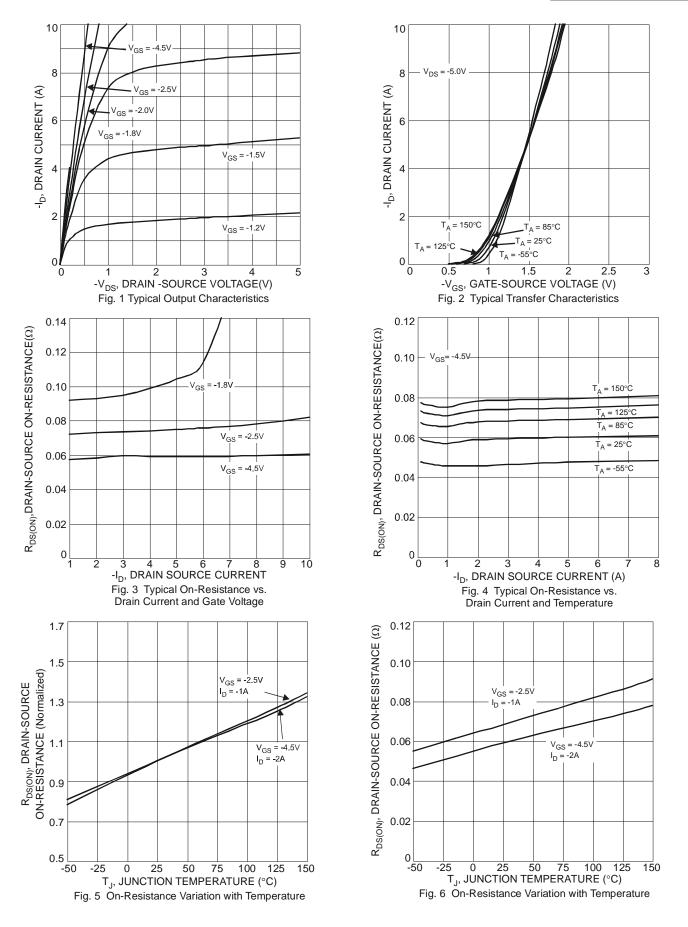
Characteristic		Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)			•			•	
Drain-Source Breakdown Voltage		BV <sub>DSS</sub>	-20	-	-	V	$V_{GS} = 0V, I_D = -250\mu A$
Zero Gate Voltage Drain Current	@T <sub>C</sub> = +25°C	I <sub>DSS</sub>	-	-	-1	μΑ	$V_{DS} = -16V, V_{GS} = 0V$
Gate-Source Leakage		I <sub>GSS</sub>	-	-	±100	nA	$V_{GS} = \pm 8V$ , $V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage		V <sub>GS(th)</sub>	-0.4	-0.6	-1.0	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$
				55	70		$V_{GS} = -4.5V, I_{D} = -1A$
Static Drain-Source On-Resistance		_		70	90	mΩ	$V_{GS} = -2.5V, I_{D} = -1A$
Static Drain-Source On-Resistance		R <sub>DS</sub> (ON)	-	90	110	mΩ	$V_{GS} = -1.8V, I_{D} = -1A$
				110	150		$V_{GS} = -1.5V, I_D = -1A$
Forward Transfer Admittance		Y <sub>fs</sub>	-	12	-	S	$V_{DS} = -10V, I_{D} = -1A$
Diode Forward Voltage (Note 5)		V <sub>SD</sub>	-	-0.7	-1	V	$V_{GS} = 0V, I_{S} = -1A$
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance		C <sub>iss</sub>	-	210	-	pF	101/11/01/
Output Capacitance		Coss	-	92	-	pF	$V_{DS} = -10V, V_{GS} = 0V,$ f = 1.0MHz
Reverse Transfer Capacitance		Crss	-	38	-	pF	1 = 1.000112
Series Gate Resistance		$R_{G}$		5.3	-	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$
Total Gate Charge (4.5V)		Qq	-	2.9	-	nC	15/1/
Gate-Source Charge		Q <sub>qs</sub>	-	0.3	-	nC	$V_{GS} = -4.5V, V_{DS} = -10V,$
Gate-Drain Charge		Q <sub>qd</sub>	-	0.5	-	nC	$I_D = -1A$ ,
Turn-On Delay Time		t <sub>D(on)</sub>	-	7.3	-	ns	
Turn-On Rise Time		t <sub>r</sub>	-	14.0	-	ns	$V_{DD} = -10V, V_{GS} = -4.5V,$
Turn-Off Delay Time		t <sub>D(off)</sub>	-	42.6	-	ns	$I_{DS} = -1A$ , $R_G = 20\Omega$ ,
Turn-Off Fall Time		t <sub>f</sub>	-	32	-	ns	]

Notes:

- 4. Device mounted on FR-4 PCB with minimum recommended pad layout.
  5. Device mounted on FR4 material with 1-inch² (6.45-cm²), 2-oz. (0.071-mm thick) Cu.
  6. 300ms pulse, pulse duty cycle ≤ 2%.
  7. Short duration pulse test used to minimize self-heating effect.

- 8. Guaranteed by design. Not subject to production testing.







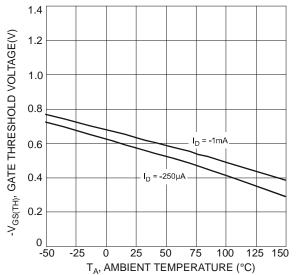
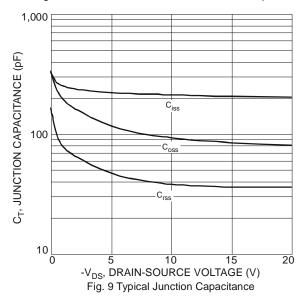
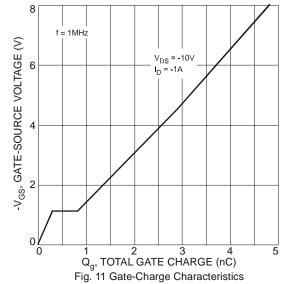
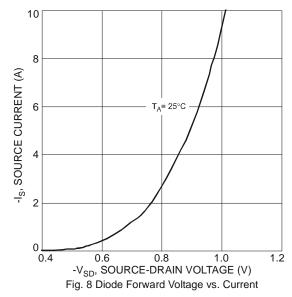


Fig. 7 Gate Threshold Variation vs. Ambient Temperature







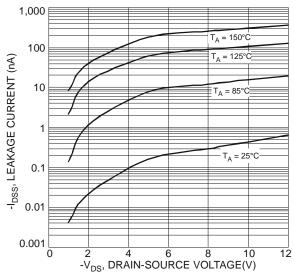
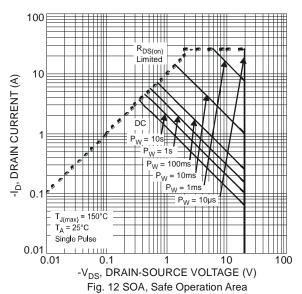
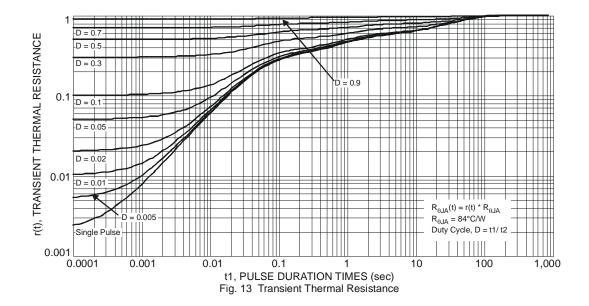


Fig. 10 Typical Drain-Source Leakage Current vs. Voltage

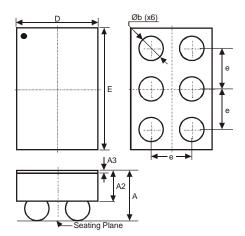






## **Package Outline Dimensions**

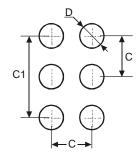
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



U-WLB1510-6							
Dim	Min	Max	Тур				
D	0.90	1.00	1.00				
Е	1.40	1.50	1.50				
Α	-	0.62	-				
A2	_	_	0.38				
A3	0.020	0.030	0.025				
b	0.27	0.37	0.32				
е	_	_	0.50				
All Dimensions in mm							

## **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	0.50
C1	1.00
D	0.25



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